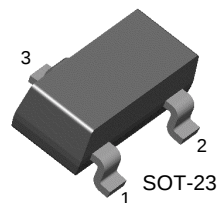


KST2484

Low Noise Transistor



1. Base 2. Emitter 3. Collector

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

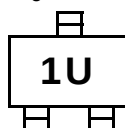
Symbol	Parameter	Value	Units
V_{CBO}	Collector Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	50	mA
P_C	Collector Power Dissipation	350	mW
T_{STG}	Storage Temperature	150	$^\circ\text{C}$

• Refer to KSP5088 for graphs

Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

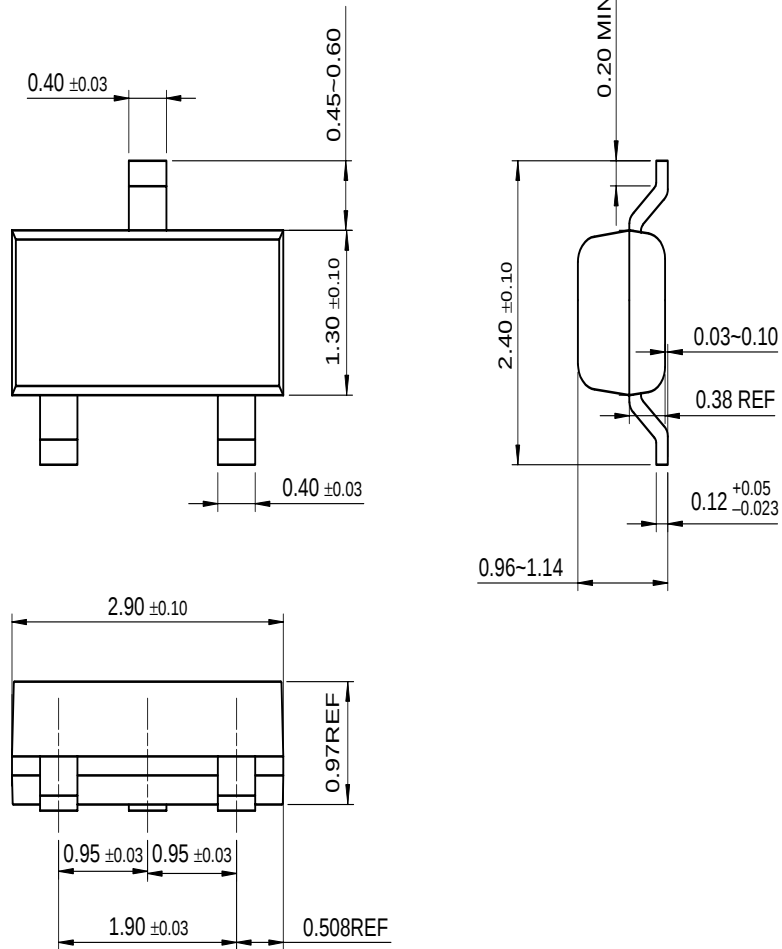
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C=10\mu\text{A}$, $I_E=0$	60		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}$, $I_B=0$	60		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=10\mu\text{A}$, $I_C=0$	5		V
I_{CBO}	Collector Cut-off Current	$V_{CB}=45\text{V}$, $I_E=0$		10	nA
I_{EBO}	Emitter Cut-off Current	$V_{EB}=5\text{V}$, $I_C=0$		10	nA
h_{FE}	DC Current Gain	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$ $V_{CE}=5\text{V}$, $I_C=10\text{mA}$	250	800	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{mA}$, $I_B=0.1\text{mA}$		0.35	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{mA}$, $V_{CE}=5\text{V}$		0.95	V
C_{ob}	Output Capacitance	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=1\text{MHz}$,		6	pF
NF	Noise Figure	$I_C=10\mu\text{A}$, $V_{CE}=5\text{V}$ $R_S=10\text{K}\Omega$, $f=1\text{KHz}$		3	dB

Marking



Package Dimensions

SOT-23



Dimensions in Millimeters